

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

Conorrol Durrocce

SCH1439 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=55m Ω (typ.)
- · 4V drive
- · Halogen free compliance
- · Protection diode in

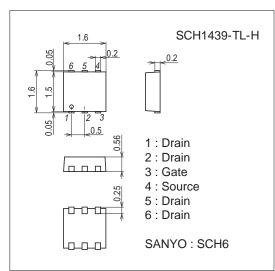
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

Package Dimensions

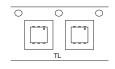
unit : mm (typ) 7028-002



Product & Package Information

Package : SCH6
 JEITA, JEDEC : SOT-563
 Minimum Packing Quantity : 5,000 pcs./reel

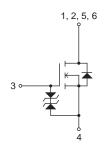
Packing Type: TL



ZQ

Marking

Electrical Connection

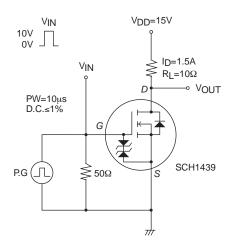


SCH1439

Electrical Characteristics at Ta=25°C

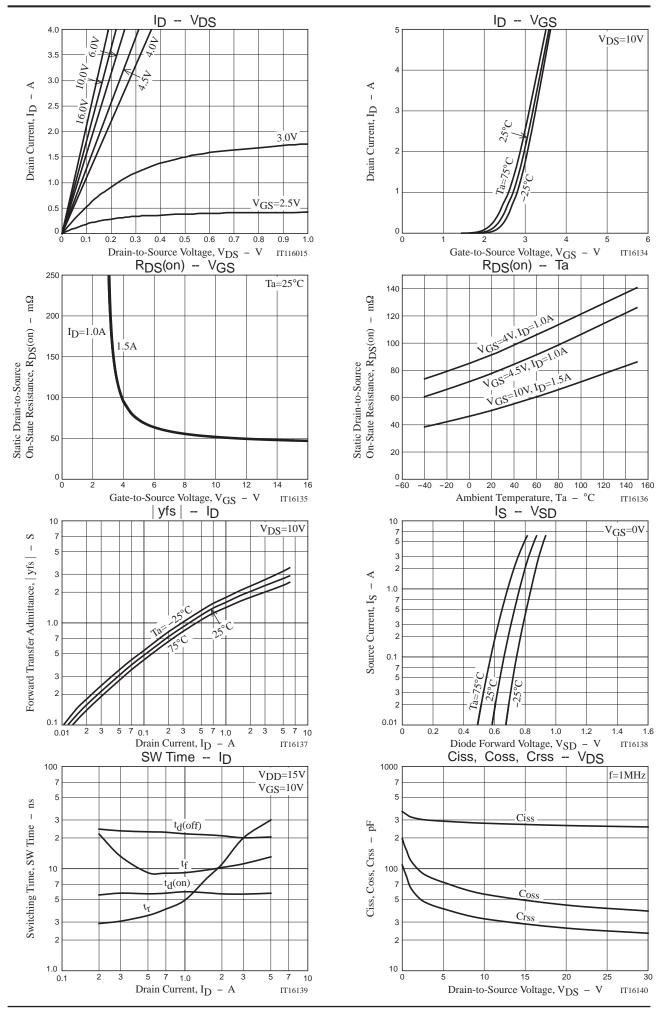
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A		1.8		S	
	R _{DS} (on)1	I _D =1.5A, V _G S=10V		55	72	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _G S=4.5V		78	110	mΩ	
	R _{DS} (on)3	I _D =1A, V _G S=4V		91	128	mΩ	
Input Capacitance	Ciss			280		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF	
Reverse Transfer Capacitance	Crss			30		pF	
Turn-ON Delay Time	t _d (on)			5.8		ns	
Rise Time	t _r	Considered Total Circuit		8.0		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		21		ns	
Fall Time	tf			9.7		ns	
Total Gate Charge	Qg			5.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =10V, I _D =3.5A		1.2		nC	
Gate-to-Drain "Miller" Charge	Qgd]		0.8		nC	
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.84	1.2	V	

Switching Time Test Circuit

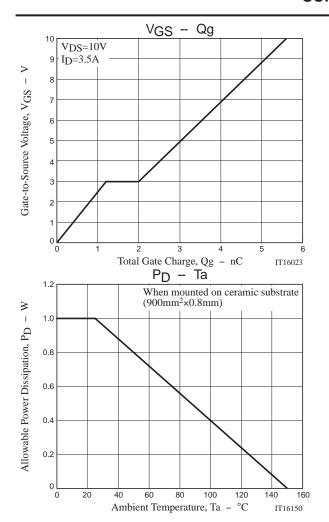


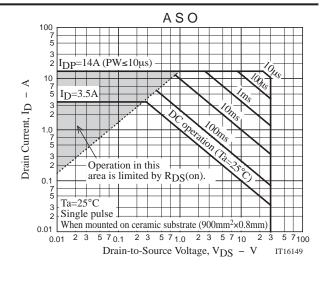
Ordering Information

Device	Package	Shipping	memo	
SCH1439-TL-H			Pb Free and Halogen Free	



SCH1439



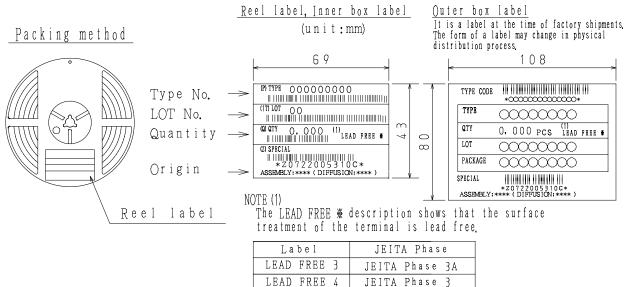


Taping Specification

SCH1439-TL-H

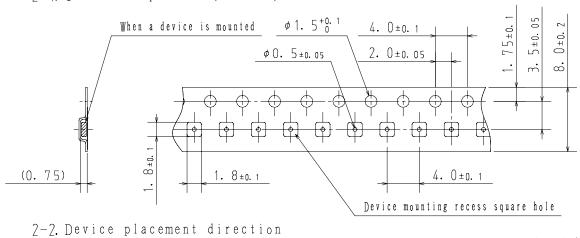
1. Packing Format

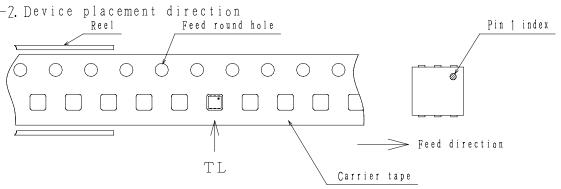
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	g format	
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
SCH6	SCH6	5,000	25, 000	150,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration

2-1. Carrier tape size (unit:mm)



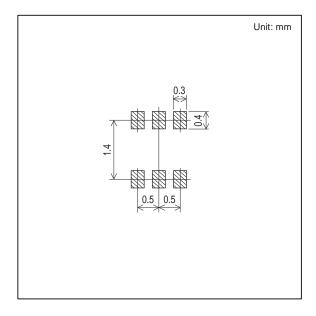


Those with pin 1 index on the feed hole side·····TL

Outline Drawing

SCH1439-TL-H

Land Pattern Example



Note on usage: Since the SCH1439 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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